

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Satoshi INOUE et al.

Application No.: 09/077,207

Filed: May 26, 1998

For: THIN FILM TRANSISTORS, LIQUID CRYSTAL DISPLAY DEVICE AND
ELECTRONIC APPARATUS USING THE SAME



Group Art Unit: 2822

Examiner: M. Prenty

Docket No.: JAO 40840

27/6 Amended
12-24-02
A. Wall

AMENDMENT UNDER 37 C.F.R. §1.111

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

In reply to the Office Action mailed July 24, 2002, the period for reply being
extended by the attached Petition for Extension of Time, please amend the above-identified
application as follows:

IN THE CLAIMS:

Please replace claim 26 as follows:

26. (Thrice Amended) A thin film transistor comprising:
- a silicon film in which a channel region is formed, the channel region
including an extension in a channel width direction;
 - a gate electrode exhibiting higher thermal conductivity than that of the silicon
film, the gate electrode formed over the channel region and covering up the extension;
 - a gate insulating film provided between the channel region and the gate
electrode;
 - a source-drain region connected to said channel region;

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